Li Wang

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/6399425/publications.pdf

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30	722	567144 15	526166 27
papers	citations	h-index	g-index

31	31	31	485
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effect of SiCâ€onâ€Si template residual stress on GaN residual stress and crystal quality. Physica Status Solidi (B): Basic Research, 2016, 253, 824-828.	0.7	1
2	Silicon etching using only Oxygen at high temperature: An alternative approach to Si micro-machining on 150â€‰mm Si wafers. Scientific Reports, 2016, 5, 17811.	1.6	6
3	Growth mechanism for alternating supply epitaxy: the unique pathway to achieve uniform silicon carbide films on multiple large-diameter silicon substrates. RSC Advances, 2016, 6, 16662-16667.	1.7	10
4	Piezo-Hall effect in single crystal p-type 3Câ€“SiC(100) thin film grown by low pressure chemical vapor deposition. RSC Advances, 2016, 6, 31191-31195.	1.7	9
5	Kinetic surface roughening and wafer bow control in heteroepitaxial growth of 3C-SiC on Si(111) substrates. Scientific Reports, 2015, 5, 15423.	1.6	13
6	Vertically Conductive Single-Crystal SiC-Based Bragg Reflector Grown on Si Wafer. Scientific Reports, 2015, 5, 17026.	1.6	13
7	Orientation dependence of the pseudo-Hall effect in p-type 3Câ€“SiC four-terminal devices under mechanical stress. RSC Advances, 2015, 5, 56377-56381.	1.7	25
8	The effect of strain on the electrical conductance of p-type nanocrystalline silicon carbide thin films. Journal of Materials Chemistry C, 2015, 3, 1172-1176.	2.7	29
9	Charge transport and activation energy of amorphous silicon carbide thin film on quartz at elevated temperature. Applied Physics Express, 2015, 8, 061303.	1.1	41
10	The effect of device geometry and crystal orientation on the stress-dependent offset voltage of 3Câ€“SiC(100) four terminal devices. Journal of Materials Chemistry C, 2015, 3, 8804-8809.	2.7	25
11	Si Surface Preparation for Heteroepitaxial Growth of SiC Using In Situ Oxidation. Materials Science Forum, 2015, 821-823, 205-208.	0.3	1
12	The Dependence of Offset Voltage in p-Type 3C-SiC van der Pauw Device on Applied Strain. IEEE Electron Device Letters, 2015, 36, 708-710.	2.2	25
13	Pseudo-Hall effect in single crystal 3C-SiC(111) four-terminal devices. Journal of Materials Chemistry C, 2015, 3, 12394-12398.	2.7	17
14	Fundamental piezoresistive coefficients of p-type single crystalline 3C-SiC. Applied Physics Letters, 2014, 104, .	1.5	70
15	Piezoresistive Effect of p-Type Single Crystalline 3C-SiC Thin Film. IEEE Electron Device Letters, 2014, 35, 399-401.	2.2	51
16	Thickness dependence of the piezoresistive effect in p-type single crystalline 3C-SiC nanothin films. Journal of Materials Chemistry C, 2014, 2, 7176-7179.	2.7	58
17	Misorientation dependent epilayer tilting and stress distribution in heteroepitaxially grown silicon carbide on silicon (111) substrate. Thin Solid Films, 2014, 564, 39-44.	0.8	19
18	Novel Electrical Characterization of Thin 3C-SiC Films on Si Substrates. Science of Advanced Materials, 2014, 6, 1542-1547.	0.1	12

#	Article	IF	Citations
19	Orientation-dependent stress relaxation in hetero-epitaxial 3C-SiC films. Applied Physics Letters, 2013, 102, .	1.5	59
20	Dependence of chemical composition and bonding of amorphous SiC on deposition temperature and the choice of substrate. Journal of Non-Crystalline Solids, 2011, 357, 1063-1069.	1.5	11
21	Demonstration of p-type 3Câ€“SiC grown on 150mm Si(100) substrates by atomic-layer epitaxy at 1000Â°C. Journal of Crystal Growth, 2011, 329, 67-70.	0.7	63
22	Growth of 3Câ€“SiC on 150-mm Si(100) substrates by alternating supply epitaxy at 1000 Â°C. Thin Solid Films, 2011, 519, 6443-6446.	0.8	94
23	InGaN/GaN Multiple Quantum Well Blue LEDs on 3C-SiC/Si Substrate. Materials Science Forum, 2011, 679-680, 801-803.	0.3	0
24	Transition between amorphous and crystalline phases of SiC deposited on Si substrate using H3SiCH3. Journal of Crystal Growth, 2009, 311, 4442-4446.	0.7	22
25	Aluminum induced in situ crystallization of amorphous SiC. Applied Physics Letters, 2009, 94, .	1.5	13
26	Deep void formation mechanism in Si(100) during its carbonization reaction with C2H2. Thin Solid Films, 2007, 515, 6824-6826.	0.8	3
27	Polytype Control in 6H-SiC Grown via Sublimation Method. Materials Science Forum, 2006, 527-529, 95-98.	0.3	6
28	Stacking faults in SiC crystal grown by spontaneous nucleation sublimation method. Journal of Crystal Growth, 2006, 292, 192-196.	0.7	16
29	Identification of Polytypes in Sublimation Grown 4H-SiC Crystals by High Resolution X-Ray Diffractometry. Materials Science Forum, 2006, 527-529, 451-454.	0.3	2
30	Color Chart for Thin SiC Films Grown on Si Substrates. Materials Science Forum, 0, 740-742, 279-282.	0.3	7